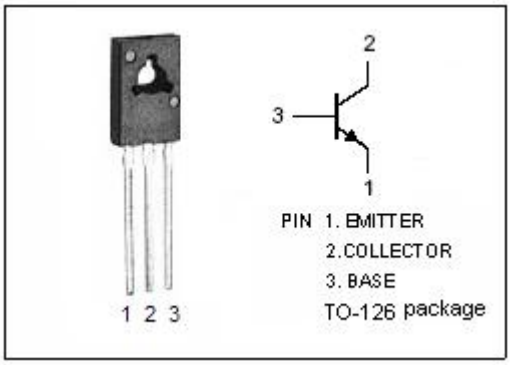
isc Silicon NPN Power Transistor — 2SD1619



DESCRIPTION

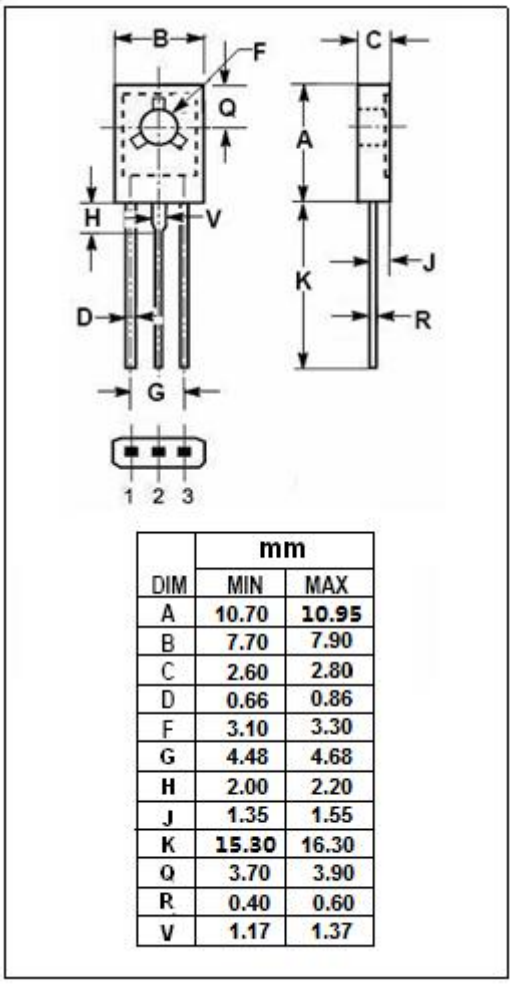
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 25V (Min)
- Complement to Type 2SB1119
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for L_F Amp Electronic Governor applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	25	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	1	A
I_{CM}	Collector Current-Peak	2	A
P_C	Collector Power Dissipation @ Tc=25℃	0.5	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 1mA; I_B= 0	25			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C=-10uA ,I_E=0	25			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 10uA; I_C= 0	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 500mA; I_B= 50mA			0.3	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 500mA; I_B= 50mA			1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 20V; I_E= 0			0.1	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 4V; I_C= 0			0.1	μA
h_{FE-1}	DC Current Gain	I_C= 50mA; V_{CE}= 2V	100		560	
h_{FE-2}	DC Current Gain	I_C= 1A; V_{CE}= 2V	40			
f_T	Current-Gain—Bandwidth Product	I_C= 50mA; V_{CE}= 10V		180		MHz
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 10V; f= 1.0MHz		15		pF

◆ **h_{FE-1} Classifications**

R	S	T	U
100-200	140-280	200-400	280-560

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